

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	
Filing Date	Feb. 18, 2004
First Named Inventor	Wu, Koucheng
Art Unit	2826
Examiner Name	
Attorney Docket Number	KWU003

Sheet 1 of 1

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US- 5,040,034		Yoshinori Murakami	
		US- 5,049,953		John L. Freeouf	
		US- 5,663,584		James D. Welch	
		US- 5,962,893		Ichiro Omura	
		US- 6,303,479		John P. Synder	
		US- 6,353,251		Mitsuteru Kimura	
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				

Examiner
SignatureDate
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known			
		Application Number			
		Filing Date	Feb. 18, 2004		
		First Named Inventor	Wu, Koucheng		
		Art Unit			
		Examiner Name			
Sheet	1	of	2	Attorney Docket Number	KWU003

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1	M. P. LEPSALTER and S. M. SZE, "SB-IGFET: An Insulated-Gate Field-Effect Transistor Using Schottky Barrier Contacts for Source and Drain", Proc. IEEE, pp. 1400-1402, Aug. 1968.	
	2	J. R. TUCKER, C. WANG, and P. S. CARNEY, "Silicon Field-Effect Transistor Based on Quantum Tunneling", Appl. Phys. Lett, vol. 65, no. 5, pp. 618-620, Aug. 1994.	
	3	B. WINSTEAD and U. RAVAIOLI, "Simulation of Schottky Barrier MOSFET's with a Coupled Quantum Injection/Monte Carlo Technique", IEEE Trans. Electron Devices, vol. 47, no. 6, pp. 1241-1246, Jun. 2000.	
	4	J. KEDZIERSKI, P. XUAN, E. H. ANDERSON, J. BOKOR, T.-J. KING, and C. HU, "Complementary Silicide Source/Drain Thin-Body MOSFETs for the 20nm Gate Length Regime", IEDM Tech. Digest, pp. 57-60, 2000	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known			
		Application Number			
		Filing Date	Feb. 18, 2004		
		First Named Inventor	Wu, Koucheng		
		Art Unit			
		Examiner Name			
Sheet	2	of	2	Attorney Docket Number	KWU003

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	5	J. D. PLUMMER and P. B. GRIFFIN, "Material and Process Limits in Silicon VLSI Technology", Proc. IEEE, vol. 89, no. 3, pp. 240-258, 2001.	
	6	D. J. FRANK, R. H. DENNARD, E. NOWAK, P. M. SOLOMON, Y. TAUR, and H.-S. P. WONG, "Device Scaling Limits of Si MOSFETs and Their Application Dependencies", Proc. IEEE, vol. 89, no. 3, pp. 259-288, 2001.	
	7	Semiconductor Industry Association, "International Technology Roadmap for Semiconductors 2002 Update", 2002.	
	8	Y. ZHANG, J. WANG, L. WANG, and B.-Y. NGUYEN, "Design of 10-nm-Scale Recessed Asymmetric Schottky Barrier MOSFETs", IEEE Electron Device Letters, vol. 23, no. 7, pp. 419-421, 2002.	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.